	Type	Hits	Search Text
1	BRS	10185	(hous$5 capsul$6 encapsul$5) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3) same coupl$4
2	BRS	391	(sleev$3 ferrul$4) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3) same align$5 same detect$6
3	BRS	173292	(backreflect$5 back near4 reflect$4) (reflect$5 near9 (nois$4 slop$2 angl$3))
4	BRS	861	(sleev$3 ferrul$4 connector$2) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3) same align$5 same mold$4
5	BRS	3	S1 and S2 and S4 and S5
6	BRS	9	S3 and S4
7	BRS	1481	(sleev$3 ferrul$4 connect$2) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3) same align$5 same detect$6
8	BRS	6247	(sleev$3 ferrul$4) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3) same align$5
9	BRS	65	S1 and S8 and S9 and S4
10	BRS	38	S10 and (sleev$3 ferrul$4 connect$2) same (fibers fibres waveguides) same align$5
11	BRS	38	S10 and (sleev$3 ferrul$4 connect$2) same (fibers fibres waveguides (fiber$1 near2 bundl$2)) same align$5
12	BRS	71147	(hous$5 capsul$6 encapsul$5) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3)
13	BRS	181011	(backreflect$5 back near4 reflect$4) (reflect$5 near12 (nois$4 slop$2 angl$3))
14	BRS	51526	align$5 same mold$4
15	BRS	7	S2 and S13 and S14 and S15

	DBs	Time Stamp
1	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:23
2	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:27
3	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:24
4	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:58
5	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:26
6	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 13:24
7	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 13:34
8	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 13:32
9	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 13:33
10	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 13:45
11	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 13:48
12	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:23
13	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:31
14	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:25
15	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:31

	Type	Hits	Search Text
16	BRS	251833	(backreflect$5 back near4 reflect$4) (reflect$5 same (nois$4 slop$2 angl$3))
17	BRS	0	S18 not S17
18	BRS	3	S18 not S16
19	BRS	19	(sleev$3 ferrul$4 connector$2) near7 slope same (reflect$5 nois$3)
20	BRS	0	S2 and S13 and S19 and S15
21	BRS	0	S2 and S13 and S19 and S21
22	BRS	0	S2 and S13 and S21 and S15
23	BRS	1	S2 and S13 and S21
24	BRS	33559	(sleev$3 ferrul$4 connector$2) near7 (angl$2 slope)
25	BRS	31	(sleev$3 ferrul$4 connector$2) same (fiber$1 fibre$1 waveguide$1 wave near1 guid$3) same align$5 same detect$6 same mold$4
26	BRS	2	"6641310".pn.
27	BRS	4	("6641310" "5917976").pn.
28	BRS	4	("6641310" "5917976").pn.
29	BRS	2	("6641310" "5917976").pn.
30	BRS	1173	(sleev$3 ferrul$4 coupler connector) near5 (slope)
31	BRS	11	S5 and S31
32	BRS	146	(sleev$3 ferrul$4 coupler connector) near4 end$1 near4 (angle$1 slope$1) same reflect$5
33	BRS	49	(S1 S2 S5) and S33
34	BRS	3	S1 and (S2 S5) and S33
35	BRS	10	S2 and S13 and S17 and S15

	DBs	Time Stamp
16	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:31
17	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:32
18	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:32
19	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:37
20	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:34
21	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:34
22	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:36
23	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:36
24	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:56
25	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:46
26	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:46
27	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:47
28	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:47
29	US-PGPUB; USPAT	2005/03/17 14:49
30	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 15:10
31	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 14:58
32	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 15:11
33	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 15:40
34	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 15:40
35	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 15:44

	Type	Hits	Search Text
36	BRS	27	("20030063832" "6782146" "5857050" "20050013551" "6017154" "6425696" "6641310" "20050013551" "5857050" "20020025125" "20040028349" "5857050" "5631991" "4215937" "20040028349" "20030021537" "20020106149" "6603906" "5631991" "4215937" "20040028349" "20030021537" "20020106149" "6603906" "5631991" "4215937").pn.
37	BRS	14	("20030063832" "6782146" "5857050" "20050013551" "6017154" "6425696" "6641310" "20050013551" "5857050" "20020025125" "20040028349" "5857050" "5631991" "4215937" "20040028349" "20030021537" "20020106149" "6603906" "5631991" "4215937" "20040028349" "20030021537" "20020106149" "6603906" "5631991" "4215937").pn.
38	BRS	1	10/663665
39	BRS	1	S38 and (connect$5 same align$5)

	DBs	Time Stamp
36	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/17 15:48
37	US-PGPUB; USPAT	2005/03/18 11:15
38	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/18 11:50
39	US-PGPUB; USPAT; EPO; JPO; DERWENT	2005/03/18 11:51

Day : Friday
Date: 3/18/2005

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Time: 15:54:44

Inventor Name Search Result

Your Search was:

Last Name = WU
First Name = SHYE-LIN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
07939244	5347161	150	09/02/1992	STACKED-LAYER STRUCTURE POLYSILICON EMITTER CONTACTED P-N JUNCTION DIODE	WU, SHYE-LIN
07987905	Not Issued	161	12/04/1992	STACKED-LAYER STRUCTURE POLYSILICON EMITTER CONTACTED P-N JUNCTION DIODE	WU, SHYE-LIN
08096505	5429966	150	07/22/1993	METHOD OF FABRICATING A TEXTURED TUNNEL OXIDE FOR EEPROM APPLICATIONS	WU, SHYE-LIN
08150385	Not Issued	161	11/09/1993	MOS TRANSISTOR WITH STACKED-SILICON LAYERS OF GATE STRUCTURE	WU, SHYE-LIN
08213855	Not Issued	161	03/16/1994	TUNNEL OXYNITRIDE STRUCTURE AND METHOD FOR FABRICATING THE SAME	WU, SHYE-LIN
08297121	Not Issued	161	08/29/1994	TUNNEL OXYNITRIDE STRUCTURE AND METHOD FOR FABRICATING THE SAME	WU, SHYE-LIN
08585033	5650351	150	01/11/1996	METHOD TO FORM A CAPACITOR HAVING MULTIPLE PILLARS FOR ADVANCED DRAMS	WU, SHYE-LIN
08623678	5656536	150	03/29/1996	METHOD OF MANUFACTURING A CROWN SHAPED CAPACITOR WITH HORIZONTAL FINS FOR HIGH DENSITY DRAMS	WU, SHYE-LIN
08624946	5585295	150	03/29/1996	METHOD FOR FORMING INVERSE-T GATE LIGHTLY-DOPED DRAIN (ITLDD) DEVICE	WU, SHYE-LIN

08624953	Not Issued	161	03/29/1996	CROWN SHAPED CAPACITOR WITH HORIZONTAL FINS FOR HIGH DENSITY DRAMS	WU, SHYE-LIN
08626164	5658822	150	03/29/1996	LOCOS METHOD WITH DOUBLE POLYSILICON/SILICON NITRIDE SPACER	WU, SHYE-LIN
08644807	Not Issued	161	05/10/1996	METHOD FOR FORMING A SHALLOW JUNCTION	WU, SHYE-LIN
08658861	Not Issued	161	05/31/1996	METHOD FOR FORMING POLYCIDE GATE	WU, SHYE-LIN
08685306	5837585	150	07/23/1996	METHOD OF FABRICATING FLASH MEMORY CELL	WU, SHYE-LIN
08708236	5933742	150	09/06/1996	MULTI-CROWN CAPACITOR FOR HIGH DENSITY DRAMS	WU, SHYE-LIN
08709161	Not Issued	161	09/06/1996	PROCESS FOR FORMING SELF-ALIGNED TWIN-TUB WITH SMOOTH SURFACE TOPOGRAPHY	WU, SHYE-LIN
08709169	5747377	150	09/06/1996	PROCESS FOR FORMING SHALLOW TRENCH ISOLATION	WU, SHYE-LIN
08746856	Not Issued	161	11/18/1996	STRUCTURE OF POROUS-SI CAPACITORS FOR HIGH DENSITY DRAMS CELL	WU, SHYE-LIN
08746857	5723373	150	11/18/1996	METHOD OF MAKING POROUS-SI CAPACITORS FOR HIGH DENSITY DRAMS CELL	WU, SHYE-LIN
08746858	5814549	150	11/18/1996	METHOD OF MAKING POROUS-SI CAPACITOR DRAM CELL	WU, SHYE-LIN
08757102	5721168	150	12/02/1996	METHOD FOR FORMING A RING-SHAPE CAPACITOR	WU, SHYE-LIN
08759615	5759893	150	12/05/1996	METHOD OF FABRICATING A RUGGED-CROWN SHAPED CAPACITOR	WU, SHYE-LIN
08763282	5679601	150	12/10/1996	LOCOS METHOD USING ENCAPSULATING POLYSILICON/SILICON NITRIDE SPACER	WU, SHYE-LIN
08783754	5670397	150	01/16/1997	DUAL POLY-GATE DEEP SUBMICRON CMOS WITH BURIED CONTACT TECHNOLOGY	WU, SHYE-LIN
08825720	5854101	150	04/04/1997	LOW MASK COUNT CMOS PROCESS WITH INVERSE-T	WU, SHYE-LIN

				GATE LDD STRUCTURE	
08859753	5736446	150	05/21/1997	METHOD OF FABRICATING A MOS DEVICE HAVING A GATE-SIDE AIR-GAP STRUCTURE	WU, SHYE-LIN
08859754	5773348	150	05/21/1997	METHOD OF FABRICATING A SHORT-CHANNEL MOS DEVICE	WU, SHYE-LIN
08877127	Not Issued	161	06/17/1997	METHOD FOR FORMING NESTED CAPACITOR AND DEVICE FORMED THEREBY	WU, SHYE-LIN
08881753	5849617	150	06/24/1997	METHOD FOR FABRICATING A NESTED CAPACITOR	WU, SHYE-LIN
08881774	5750431	150	06/24/1997	METHOD FOR FABRICATING A STACKED CAPACITOR	WU, SHYE-LIN
08881776	5756388	150	06/24/1997	METHOD FOR FABRICATING A RAKE-SHAPED CAPACITOR	WU, SHYE-LIN
08906552	5937281	150	08/05/1997	METHOD TO FORM METAL-TO-METAL ANTIFUSE FOR FIELD PROGRAMMABLE GATE ARRAY APPLICATIONS USING LIQUID PHASE DEPOSITION (LPD)	WU, SHYE-LIN
08935544	6033956	150	09/23/1997	METHOD TO FORM CONTACTLESS ARRAY FOR HIGH DENSITY NONVOLATILE MEMORIES	WU, SHYE-LIN
08953609	5915182	150	10/17/1997	MOSFET WITH SELF-ALIGNED SILICIDATION AND GATE-SIDE AIR-GAP STRUCTURE	WU, SHYE-LIN
08954412	5930622	150	10/20/1997	METHOD FOR FORMING A DRAM CELL WITH A DOUBLE-CROWN SHAPED CAPACITOR	WU, SHYE-LIN
08954413	5866455	150	10/20/1997	METHOD FOR FORMING A DRAM CELL WITH A MULTIPLE PILLAR-SHAPED CAPACITOR	WU, SHYE-LIN
08954416	5834353	150	10/20/1997	METHOD OF MAKING DEEP SUB-MICRON METER MOSFET WITH A HIGH PERMITIVITY GATE DIELECTRIC	WU, SHYE-LIN
08954448	Not Issued	161	10/20/1997	METHOD FOR FORMING A RUGGED STACKED TRENCH (RST) CAPACITOR OF A DRAM CELL	WU, SHYE-LIN
08958536	6027981	150	10/27/1997	METHOD FOR FORMING A	WU, SHYE-LIN

				DRAM CELL WITH A FORK-SHAPED CAPACITOR	
08960870	6011286	150	10/31/1997	DOUBLE STAIR-LIKE CAPACITOR STRUCTURE FOR A DRAM CELL	WU, SHYE-LIN
08962003	6020609	150	10/31/1997	DRAM CELL WITH A RUGGED STACKED TRENCH (RST) CAPACITOR	WU, SHYE-LIN
08962623	5766995	150	11/03/1997	METHOD FOR FORMING A DRAM CELL WITH A RAGGED POLYSILICON CROWN-SHAPED CAPACITOR	WU, SHYE-LIN
08962625	5807777	150	11/03/1997	METHOD OF MAKING A DOUBLE STAIR-LIKE CAPACITOR FOR A HIGH DENSITY DRAM CELL	WU, SHYE-LIN
08984871	6180988	150	12/04/1997	SELF-ALIGNED SILICIDED MOSFETS WITH A GRADED S/D JUNCTION AND GATE-SIDE AIR-GAP STRUCTURE	WU, SHYE-LIN
08990117	5913118	150	12/12/1997	METHOD OF MANUFACTURING TRENCH DRAM CELLS WITH SELF-ALIGNED FIELD PLATE	WU, SHYE-LIN
08990167	6100127	150	12/12/1997	SELF-ALIGNED SILICIDED MOS TRANSISTOR WITH A LIGHTLY DOPED DRAIN BALLAST RESISTOR FOR ESD PROTECTION	WU, SHYE-LIN
08994053	5856226	150	12/19/1997	METHOD OF MAKING ULTRA-SHORT CHANNEL MOSFET WITH SELF-ALIGNED SILICIDED CONTACT AND EXTENDED S/D JUNCTION	WU, SHYE-LIN
08994178	6087234	150	12/19/1997	METHOD OF FORMING A SELF-ALIGNED SILICIDE MOSFET WITH AN EXTENDED ULTRA-SHALLOW S/D JUNCTION	WU, SHYE-LIN
08995569	5966612	150	12/22/1997	METHOD OF MAKING A MULTIPLE MUSHROOM SHAPE CAPACITOR FOR HIGH DENSITY DRAMS	WU, SHYE-LIN
08996694	6022769	150	12/23/1997	METHOD OF MAKING SELF-ALIGNED SILICIDED MOS TRANSISTOR WITH ESD PROTECTION IMPROVEMENT	WU, SHYE-LIN

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